

AMENDMENTS TO THE SPECIFICATION

Replace the paragraph starting on page 5, line 23 and ending on page 6, line 11 with the following replacement paragraph:

Another aspect of the present invention a method of forming an opening in a layer of a first material of a semiconductor device: providing the layer of the first material; forming a layer of a second material over the layer of the first material; forming a layer of a third material over the layer of the second material; forming a sidewall surface in the layer of the third material; forming a sidewall spacer of a ~~forth~~ fourth material on the sidewall surface; forming a layer of a fifth material over the sidewall spacer and an exposed portion of the layer of the second material; removing a portion of the fifth material to expose the sidewall spacer; removing the sidewall spacer; removing a portion of the layer of the second material exposing the layer of the first material; and removing a portion of the layer of the first material to form the opening.

Replace the paragraph starting on page 6, line 12 and ending on page 6, line 22 with the following replacement paragraph:

Another aspect of the present invention is a method of forming an opening in a layer of a first material of a semiconductor device: providing the layer of the first

material; forming a layer of a second material over the layer of the first material; forming a sidewall surface in the layer of the second material; forming a sidewall spacer of a third material on the sidewall surface; forming a layer of a ~~forth~~ fourth material over the sidewall spacer and an exposed portion of the layer of the first material; removing a portion of the ~~forth~~ fourth material to expose the sidewall spacer; removing the sidewall spacer; and removing a portion of the layer of the first material to form the opening.

Replace the paragraph starting on page 6, line 23 and ending on page 7, line 15 with the following replacement paragraph:

Another aspect of the present invention is a method of forming a programmable resistance memory element, comprising the steps of: providing a layer of a conductive material; forming a layer of a first material over the layer of the conductive material; forming a layer of a second material over the layer of the first material; forming a layer of a third material over the layer of the second material; forming a sidewall surface in the layer of the third material; forming a sidewall spacer of a ~~forth~~ fourth material on the sidewall surface; forming a layer of a fifth material over the sidewall spacer and an exposed portion of the layer of the second material; removing a portion of the fifth material to expose the sidewall spacer; removing the sidewall spacer;

removing a portion of the layer of the second material exposing the layer of the first material; removing a portion of the layer of the first material to form the opening; and depositing a programmable resistance material into the opening, the programmable resistance material in communication with the layer of the conductive material.

Replace the paragraph starting on page 7, line 16 and ending on page 8, line 5 with the following replacement paragraph:

Another aspect of the present invention is a method of forming a programming resistance memory element, comprising the steps of: providing a layer of a conductive material; forming a layer of a first material over the layer of the conductive material; forming a layer of a second material over the layer of the first material; forming a sidewall surface in the layer of the second material; forming a sidewall spacer of a third material on the sidewall surface; forming a layer of a ~~forth~~ fourth material over the sidewall spacer and an exposed portion of the layer of the first material; removing a portion of the ~~forth~~ fourth material to expose the sidewall spacer; removing the sidewall spacer; removing a portion of the layer of the first material to form the opening; and depositing a programmable resistance material into the opening, the programmable resistance

material in communication the layer of the conductive material.

Replace the paragraph starting on page 8, line 6 and ending on page 8, line 8 with the following replacement paragraph:

It is noted that the two or more of the first, second, third, ~~forth~~ fourth, and fifth materials may be the same material (or each may be a different material).